

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

KEY PARAMETERS

V_{DRM}	5200V
I_{T(AV)}	1950A
I_{TSM}	26200A
dV/dt*	1500V/μs
dI/dt	300A/μs

* Higher dV/dt selections are available on request

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages V _{DRM} and V _{RRM} (V)	Conditions
DCR1950C52*	5200	T _{vj} = -40°C to 125°C, I _{DRM} = I _{RRM} = 300mA, V _{DRM} , V _{RRM} t _p = 10ms V _{DSM} & V _{RSM} = V _{DRM} & V _{RRM} + 100V respectively
DCR1950C50	5000	
DCR1950C48	4800	

Lower voltage grades available.

*5000V @ -40°C, 5200V @ 0°C

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR1950C52

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

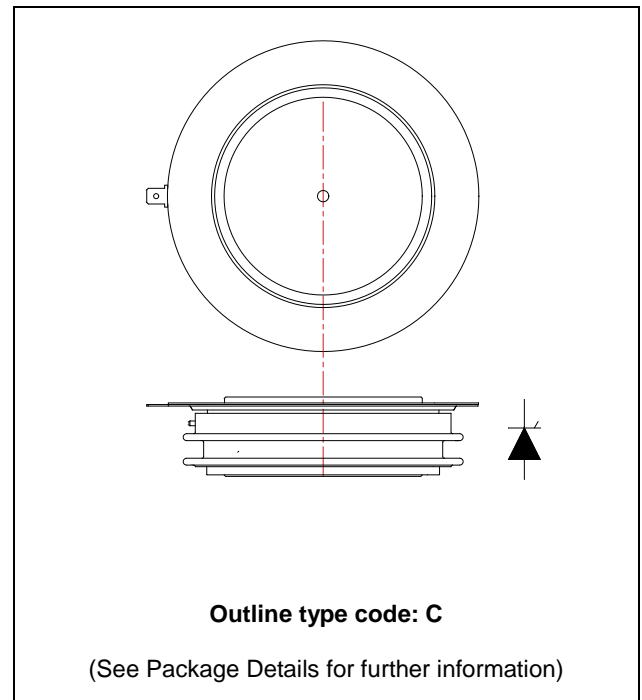


Fig. 1 Package outline

CURRENT RATINGS

$T_{case} = 60^{\circ}C$ unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Side Cooled				
$I_{T(AV)}$	Mean on-state current	Half wave resistive load	1950	A
$I_{T(RMS)}$	RMS value	-	3060	A
I_r	Continuous (direct) on-state current	-	3000	A

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
I_{TSM}	Surge (non-repetitive) on-state current	10ms half sine, $T_{case} = 125^{\circ}C$ $V_R = 0$	26.2	kA
I^2t	I^2t for fusing		3.43	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
$R_{th(j-c)}$	Thermal resistance - junction to case	Double side cooled	DC	-	10.1	$^{\circ}C/kW$
		Single side cooled	Anode DC	-	17.6	$^{\circ}C/kW$
			Cathode DC	-	23.9	$^{\circ}C/kW$
$R_{th(c-h)}$	Thermal resistance - case to heatsink	Clamping force 37kN (with mounting compound)	Double side	-	2.5	$^{\circ}C/kW$
			Single side	-	5.0	$^{\circ}C/kW$
T_{vj}	Virtual junction temperature	Blocking V_{DRM} / V_{RRM}		-	125	$^{\circ}C$
T_{stg}	Storage temperature range			-55	125	$^{\circ}C$
F_m	Clamping force			33	41	kN

DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditions	Min.	Max.	Units	
I_{RRM}/I_{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125°C	-	300	mA	
V_{TM}	Instantaneous forward voltage	At 4000A peak, T _j = 125°C	2.10	2.50	V	
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V _{DRM} , T _j = 125°C, gate open	-	1500	V/μs	
di/dt	Rate of rise of on-state current	From 67% V _{DRM} to 2x I _{T(AV)} Gate source 30V, 10Ω tr < 0.5μs, T _j = 125°C	Repetitive 50Hz	-	150	A/μs
			Non-repetitive	-	300	A/μs
V_{T(TO)}	Threshold voltage - Low level	500A to 2300A at T _{case} = 125°C	-	0.93	V	
	Threshold voltage - High level	2300A to 7000A at T _{case} = 125°C	-	1.11	V	
r_T	On-state slope resistance - Low level	500A to 2300A at T _{case} = 125°C	-	0.43	mΩ	
	On-state slope resistance - High level	2300A to 7000A at T _{case} = 125°C	-	0.35	mΩ	
t_{gd}	Delay time	V _D = 67% V _{DRM} , gate source 30V, 10Ω tr = 0.5μs, T _j = 25°C	-	3	μs	
t_q	Turn-off time	T _j = 125°C, V _R = 200V, di/dt = 1A/μs, dV _{DR} /dt = 20V/μs linear	700	1100	μs	
Q_s	Stored charge	I _T = 2000A, T _j = 125°C, di/dt = 1A/μs	1590	3520	μC	
I_{RR}	Reverse recovery current	V _R peak ~ 3100V, V _R ~ 2100V	33	51	A	
I_L	Latching current	T _j = 25°C, V _D = 5V	-	3	A	
I_H	Holding current	T _j = 25°C, R _{G-K} = ∞, I _{TM} = 500A, I _T = 5A	-	300	mA	

GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V _{GT}	Gate trigger voltage	V _{DRM} = 5V, T _{case} = 25°C	1.5	V
V _{GD}	Gate non-trigger voltage	At 50% V _{DRM} , T _{case} = 125°C	0.4	V
I _{GT}	Gate trigger current	V _{DRM} = 5V, T _{case} = 25°C	350	mA
I _{GD}	Gate non-trigger current	At 50% V _{DRM} , T _{case} = 125°C	10	mA

CURVES

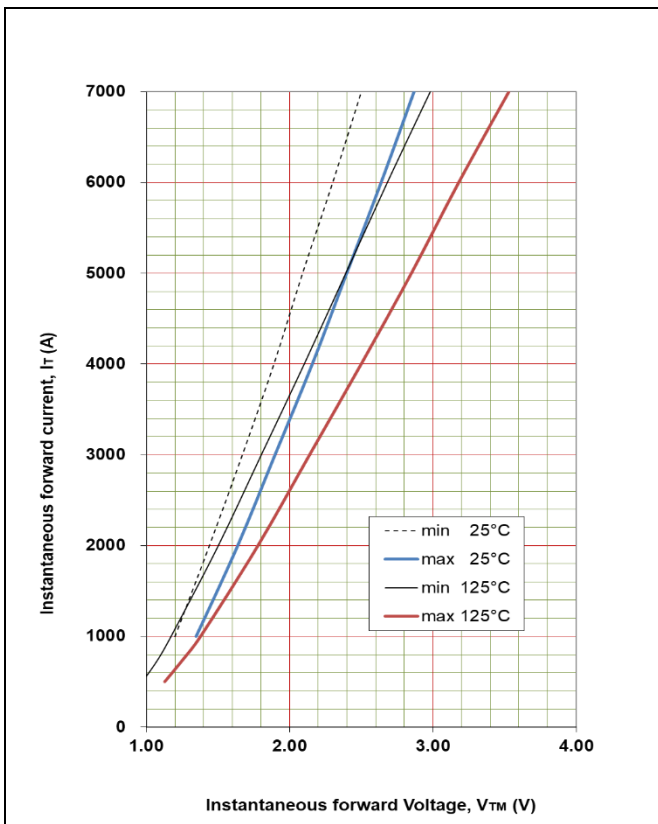


Fig. 2 Maximum & minimum on state characteristics

V_{TM} EQUATION

$$V_{TM} = A + B \cdot \ln(I_T) + C \cdot I_T + D \cdot \sqrt{I_T}$$

Where A = -0.142716

B = 0.203055

C = 0.000358

D = -0.007514

These values are valid for T_j = 125°C for I_T 500A to 7000A

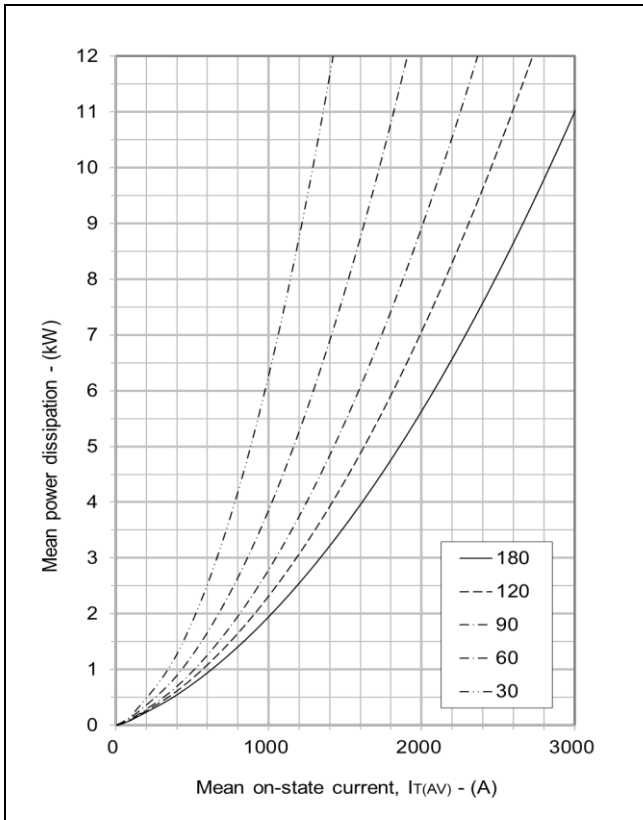


Fig. 3 On-state power dissipation - sine wave

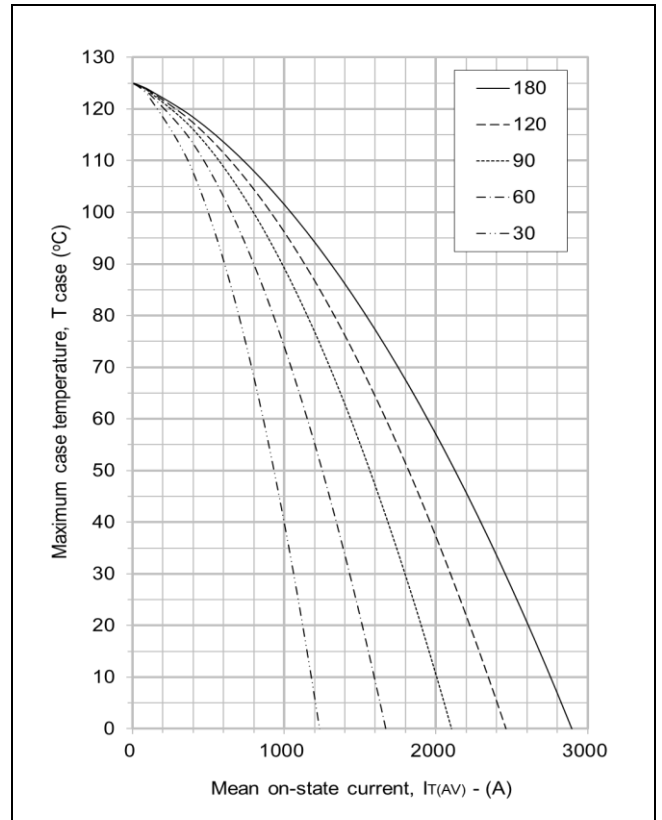


Fig. 4 Maximum permissible case temperature, double side cooled - sine wave

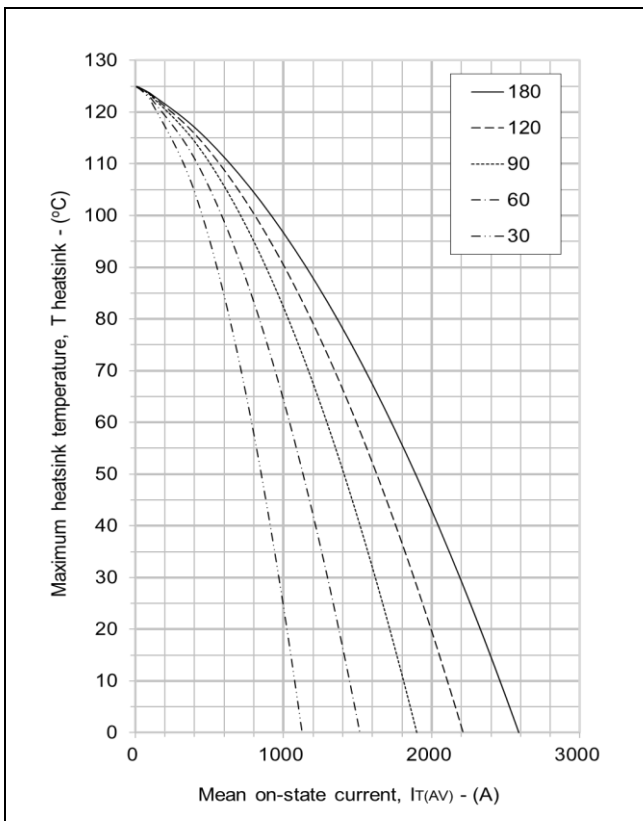


Fig. 5 Maximum permissible heatsink temperature, double side cooled - sine wave

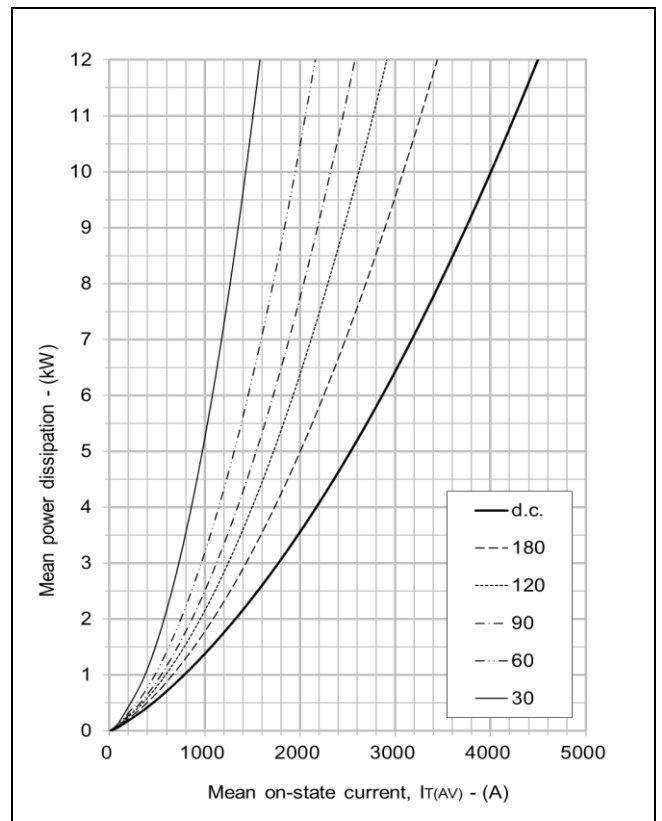


Fig. 6 On-state power dissipation - rectangular wave

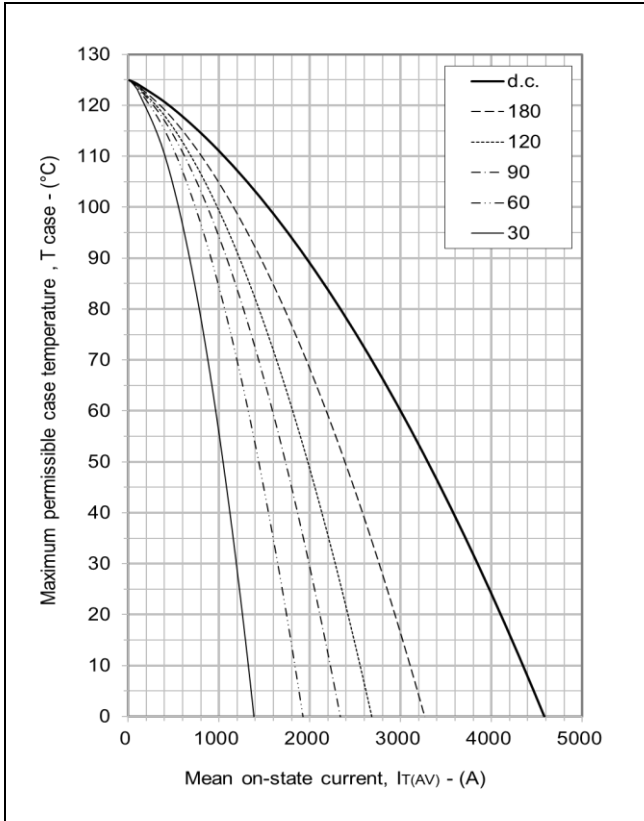


Fig. 7 Maximum permissible case temperature, double side cooled - rectangular wave

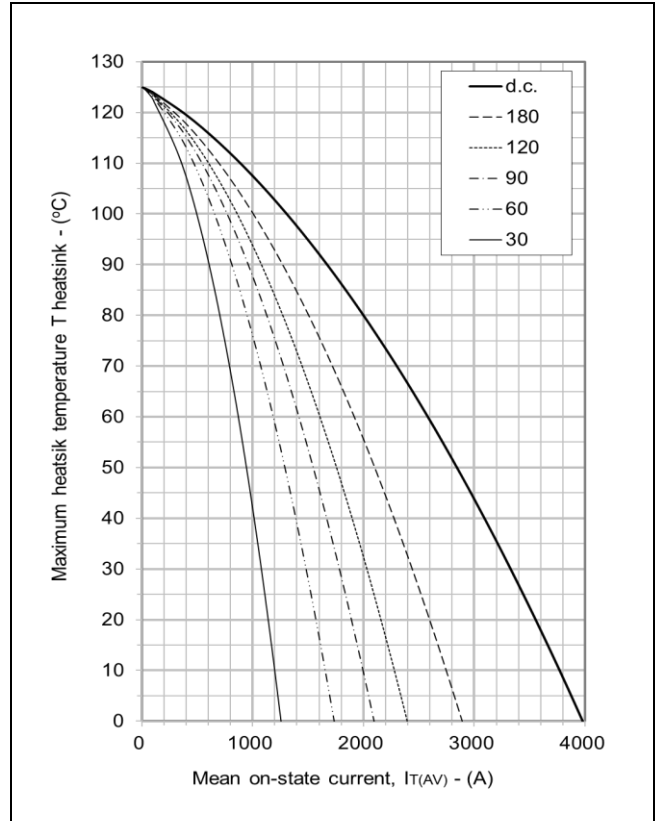


Fig. 8 Maximum permissible heatsink temperature, double side cooled - rectangular wave

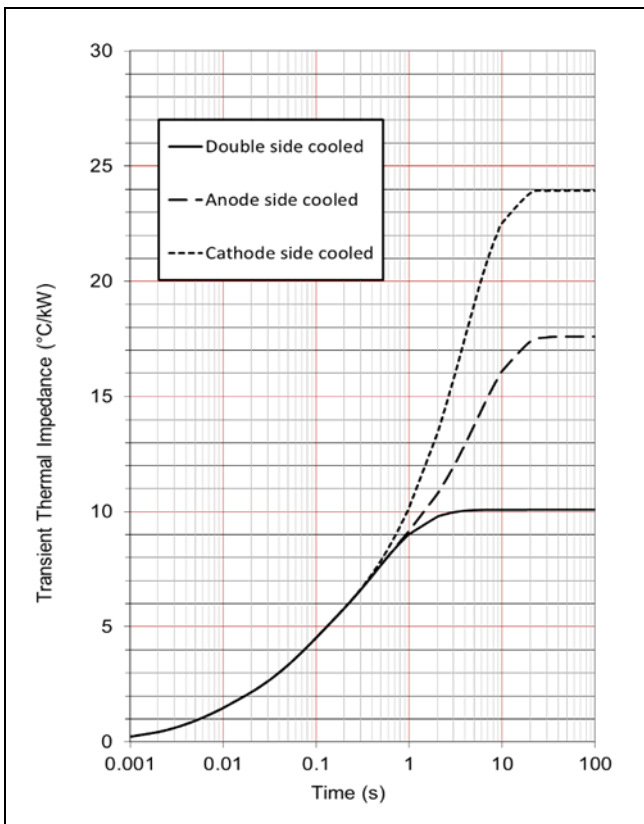


Fig. 9 Maximum (limit) transient thermal impedance – junction to case (degC/kW)

		1	2	3	4
Double side cooled	Ri(°C/kW)	1.104	2.576	4.510	1.901
	Ti(s)	0.006	0.052	0.382	1.060
Anode side cooled	Ri(°C/kW)	1.098	2.457	4.047	9.999
	Ti(s)	0.006	0.050	0.313	5.270
Cathode side cooled	Ri(°C/kW)	1.152	2.893	2.406	17.479
	Ti(s)	0.006	0.058	0.378	3.970

$$Z_{th} = \sum_{i=1}^{i=4} R_i \cdot \left(1 - \exp\left(-\frac{T}{T_i}\right)\right)$$

$\Delta R_{th(j-c)}$ Conduction

Tables show the increments of thermal resistance $R_{th(j-c)}$ when the device operates at conduction angles other than d.c.

θ°	Double side cooling		Anode Side Cooling		Cathode Sided Cooling			
	$\Delta Z_{th}(z)$		$\Delta Z_{th}(z)$		$\Delta Z_{th}(z)$			
	sine.	rect.	sine.	rect.	sine.	rect.		
180	1.95	1.26	1.95	1.26	1.95	1.26		
120	2.32	1.89	120	2.32	1.89	2.31	1.88	
90	2.74	2.27	90	2.74	2.27	90	2.72	2.26
60	3.14	2.70	60	3.14	2.70	60	3.12	2.68
30	3.46	3.19	30	3.46	3.19	30	3.43	3.17
15	3.61	3.47	15	3.62	3.47	15	3.58	3.44

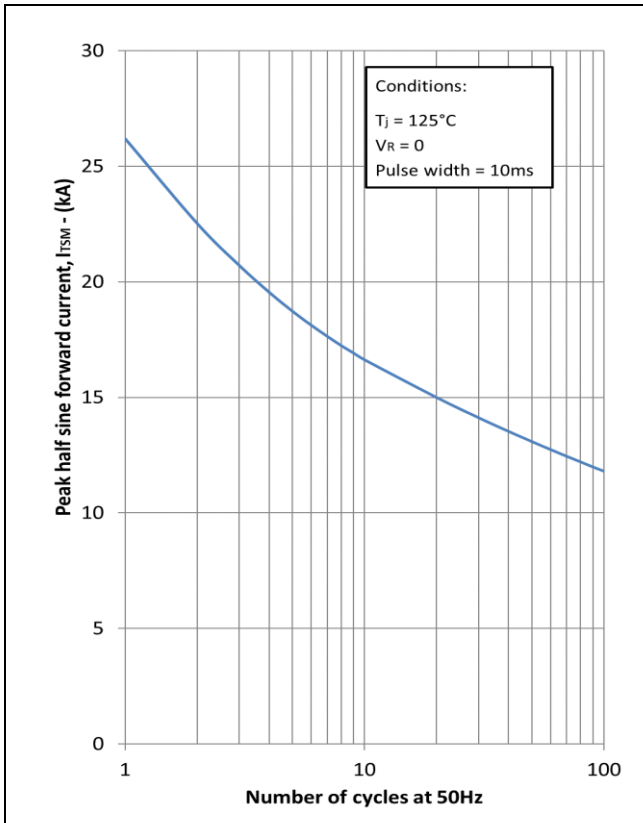


Fig. 10 Multi-cycle surge current

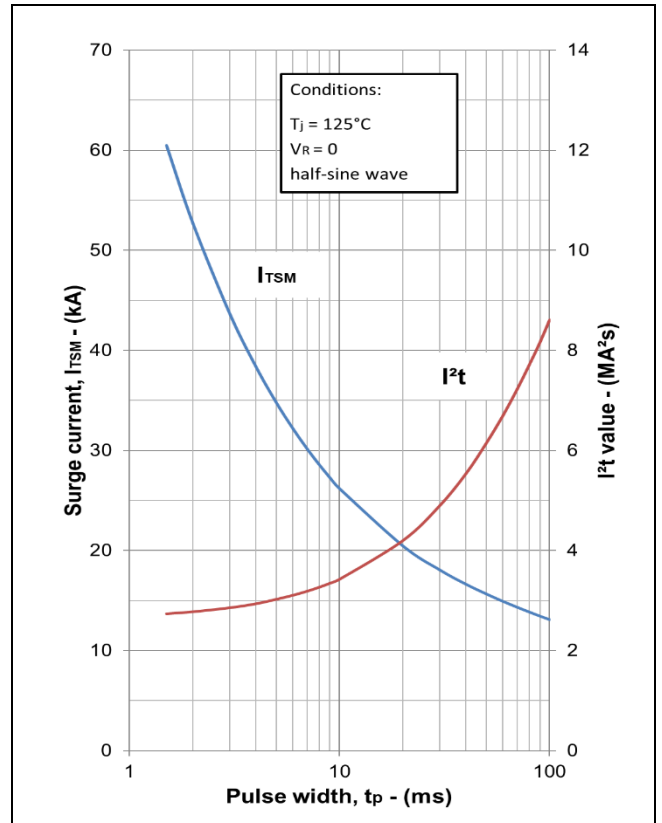


Fig. 11 Single-cycle surge current

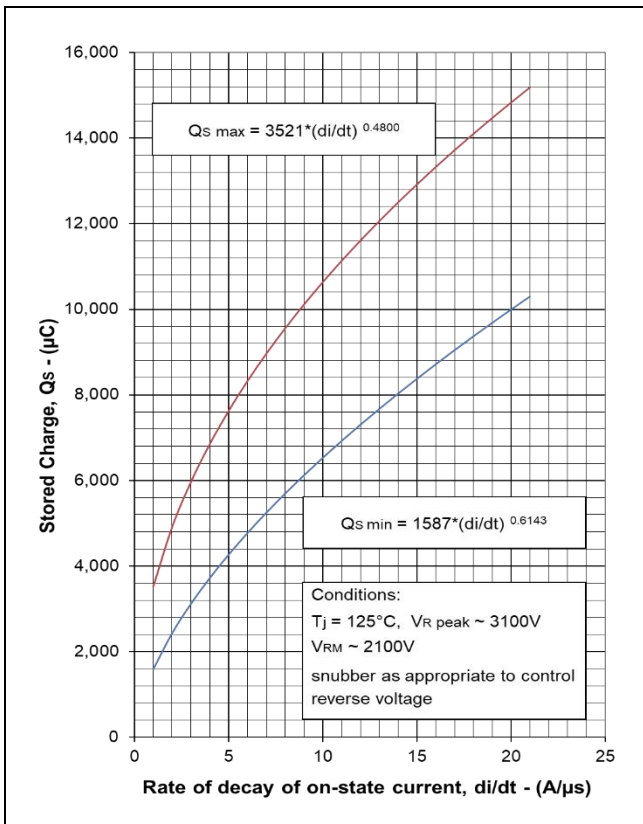


Fig. 12 Stored charge

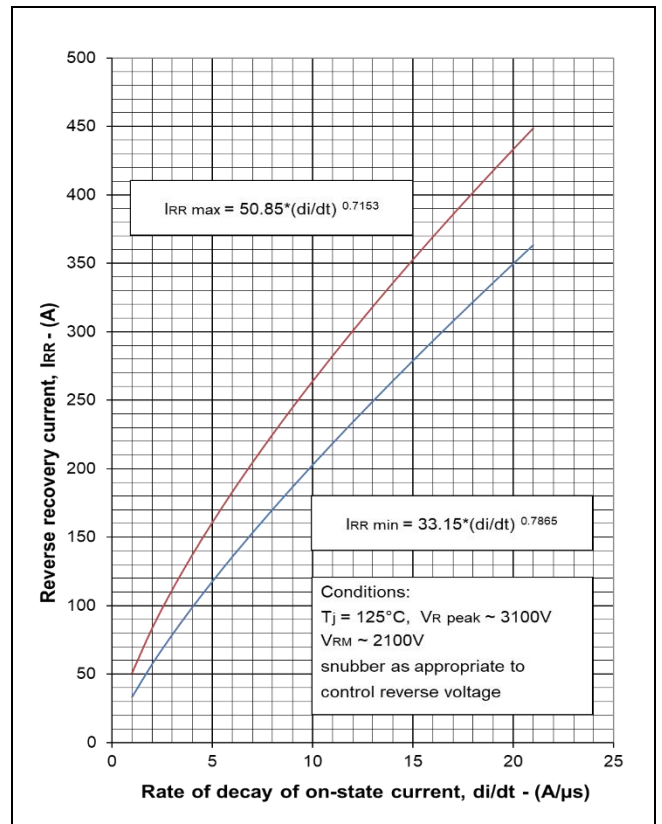


Fig. 13 Reverse recovery current

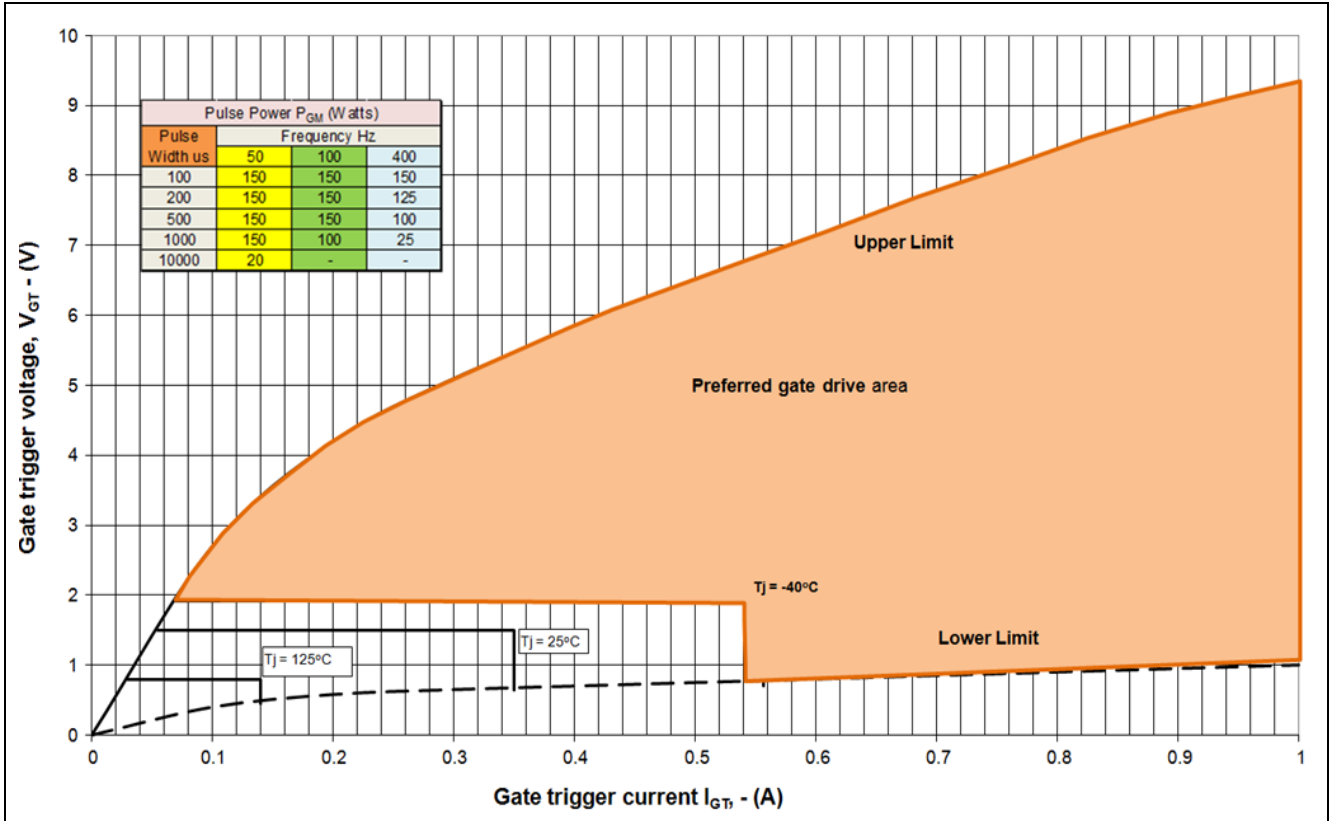


Fig. 14 Gate characteristics

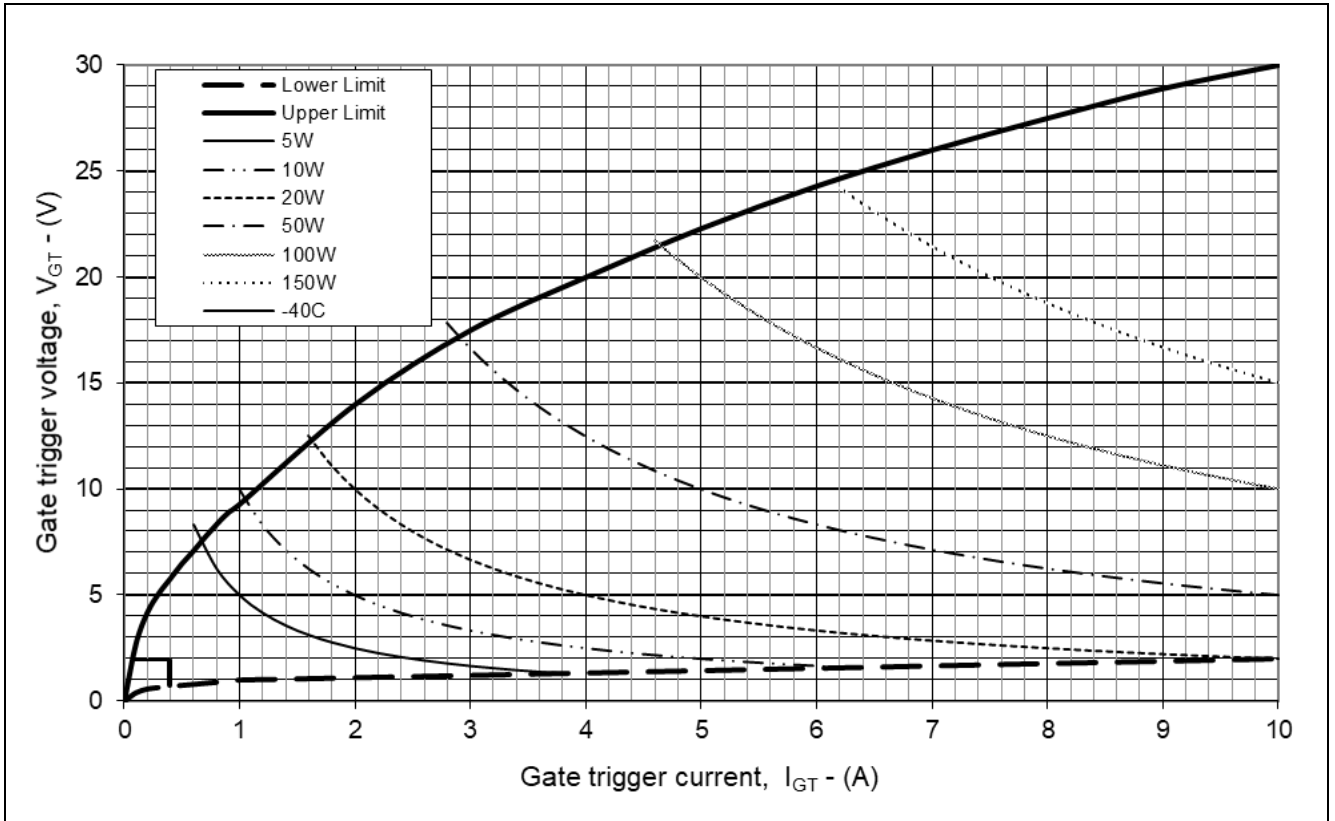


Fig. 15 Gate characteristics

PACKAGE DETAILS

For further package information, please contact Customer services.

All dimensions in mm, unless stated otherwise.

DO NOT SCALE

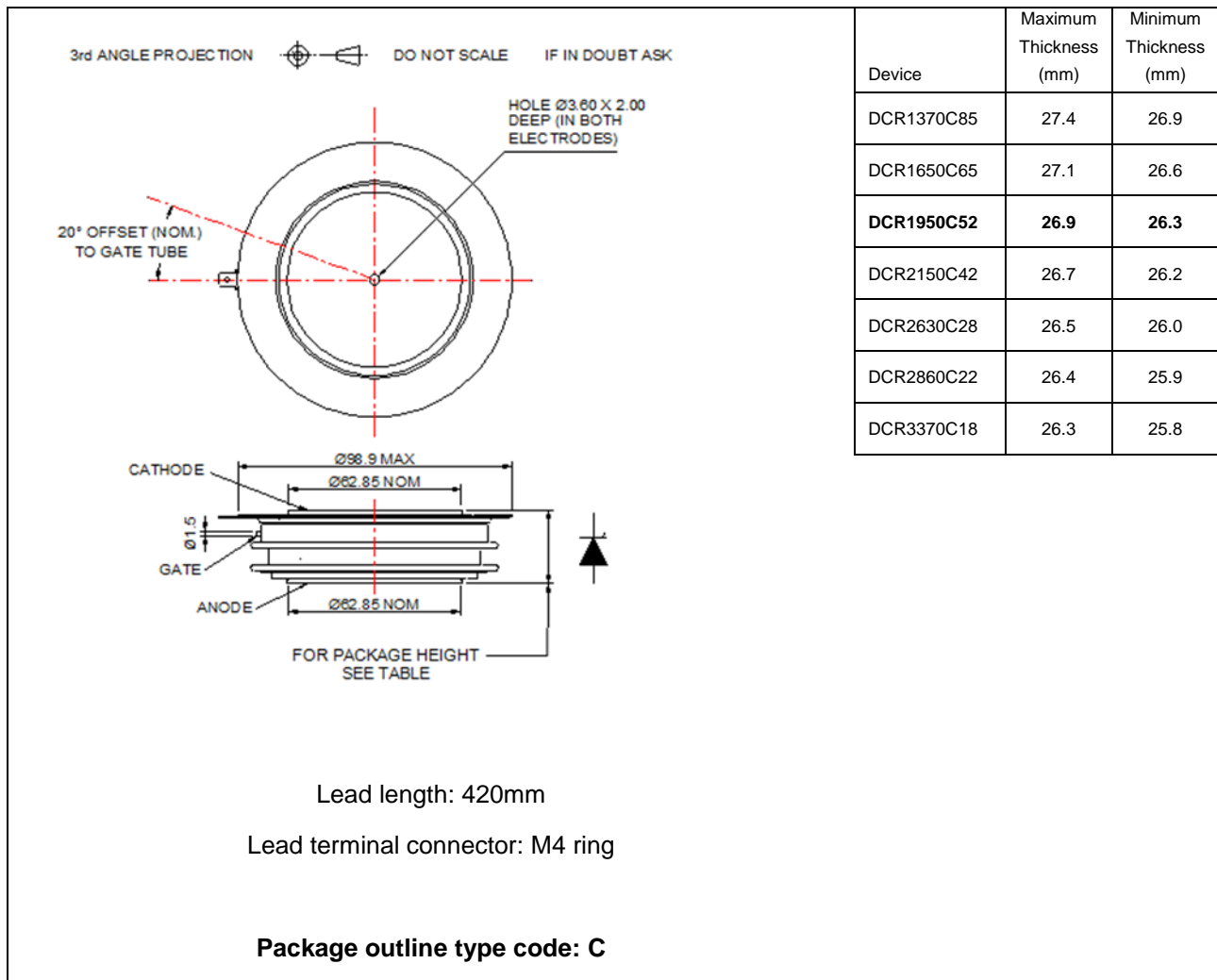


Fig. 16 Package outline

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